
Session Title:	18. Oxide TFT Mobility III
Date:	Aug. 24, 2016 (Wednesday)
Time:	14:30~16:00
Room	Room B (Halla B)
Session Chairs	Dr. Jong Uk Bae (LG Display Co., Ltd., Korea) Prof. Jin-Seong Park (Hanyang Univ., Korea)

B18-1

14:30~14:55

[Invited] High Mobility Oxide TFT for the Application to the High Resolution Active Matrix Display

Sang-Hee Ko Park, Yujin Kim, Kwang-Heum Lee, Geumbi Mun, Guk-Jin Jeon, Jae-Han Ahn (KAIST, Korea), Jae Chul Do, and Wan Woo Park (Advanced Vacuum and Clean Equipment Optimizer, Korea)

B18-2

14:55~15:20

[Invited] High Resolution Display using High Electrical and Reliable Performance Oxide Thin Film Transistors

Jun Hyung Lim, Keunkyu Song, Masataka Kano, Yeonkeon Moon, Hyunsup Lee, HyungIl Jeon, Junghun Noh, Sang Hee Jang, Byung-Seok Choi, Hye Yong Chu, and Junho Song (Samsung Display Co., Ltd., Korea)

B18-3

15:20~15:45

High Mobility Oxide Thin-Film Transistors with In-W-Zn-O Channel

Mamoru Furuta, Daichi Koretomo, Yuta Hashimoto (Kochi Univ. of Tech., Japan), Kenichi Watatani, Miki Miyanaga, and Hideaki Awata (Sumitomo Electric Industries, Ltd., Japan)

B18-4

15:45~16:00

The Relation between Phase and Electrical Properties in an InAlOx Film by Controlling Al doping Concentration for TFT Applications

GeumBi Mun, Hye-In Yeom, Jong-Beom Ko, and Sang-Hee Ko Park (KAIST, Korea)